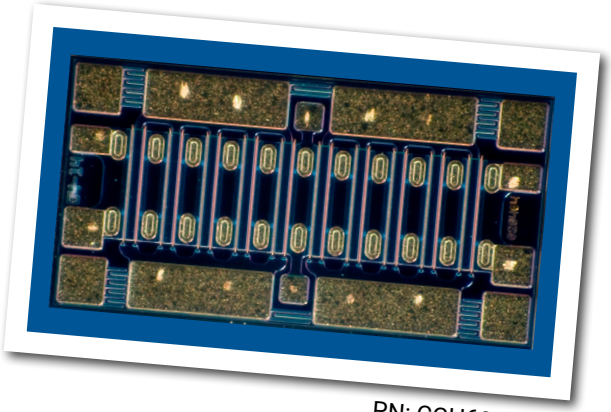
CGH60030D

30 W, 6.0 GHz, GaN HEMT Die

Cree's CGH60030D is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT). GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity, and higher thermal conductivity. GaN HEMTs offer greater power density and wider bandwidths compared to Si and GaAs transistors.



PN: CGH60030D

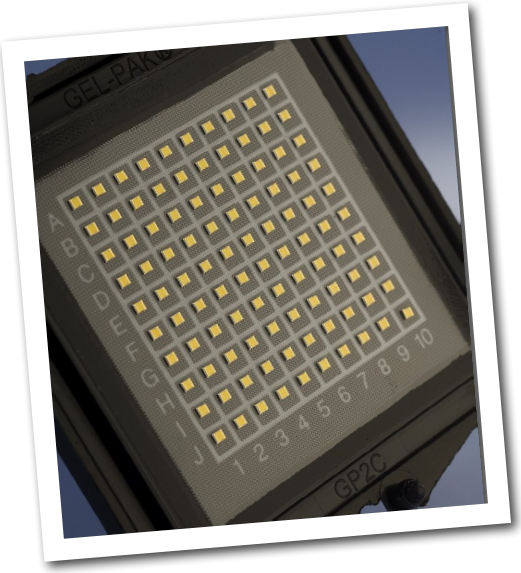
FEATURES

- 15 dB Typical Small Signal Gain at 4 GHz
- 12 dB Typical Small Signal Gain at 6 GHz
- 30 W Typical P_{SAT}
- 28 V Operation
- High Breakdown Voltage
- High Temperature Operation
- Up to 6 GHz Operation
- High Efficiency

APPLICATIONS

- 2-Way Private Radio
- Broadband Amplifiers
- Cellular Infrastructure
- Test Instrumentation
- Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

RoHS COMPLIANT



Packaging Information

- Bare die are shipped in Gel-Pak® containers.
- Non-adhesive tacky membrane immobilizes die during shipment.

Large Signal Models Available for ADS and MWO

Absolute Maximum Ratings (not simultaneous) at 25˚C

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DSS}	84	VDC	25˚C
Gate-source Voltage	V_{GS}	-10, +2	VDC	25˚C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	7.0	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	3.0	A	25˚C
Thermal Resistance, Junction to Case (packaged)[2]	$R_{\theta JC}$	4.8	˚C/W	
Thermal Resistance, Junction to Case (die only)	$R_{\theta JC}$	3.0	˚C/W	85˚C
Mounting Temperature (30 seconds)	T_S	320	˚C	30 seconds

Note[1] Current limit for long term, reliable operation

Note[2] Eutectic die attach using 80/20 AuSn mounted to a 40 mil thick CuMoCu carrier.

Electrical Characteristics (Frequency = 4 GHz unless otherwise stated; T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{GS(TH)}$	-3.8	-3.0	–2.3	V	V_{DS} = 10 V, I_D = 7.2 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DD} = 28 V, I_{DQ} = 200 mA
Drain Current	I_{DS}	5.8	7.0	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BD}	120	–	–	V	V_{GS} = -8 V, I_D = 7.2 mA
On Resistance	R_{ON}	–	0.5	–	Ω	V_{DS} = 0.1 V
Gate Forward Voltage	V_{G-ON}	–	1.9	–	V	I_{GS} = 7.2 mA
RF Characteristics						
Small Signal Gain	G_{SS}	–	15	–	dB	V_{DD} = 28 V, I_{DQ} = 200 mA
Saturated Power Output[1]	P_{SAT}	–	30	–	W	V_{DD} = 28 V, I_{DQ} = 200 mA
Drain Efficiency[2]	η	–	65	–	%	V_{DD} = 28 V, I_{DQ} = 200 mA, P_{SAT} = 30 W
Intermodulation Distortion	IM3	–	-30	–	dBc	V_{DD} = 28 V, I_{DQ} = 200 mA, P_{OUT} = 30 W PEP
Output Mismatch Stress	VSWR	–	–	10 : 1	Ψ	No damage at all phase angles, V_{DD} = 28 V, I_{DQ} = 200 mA, P_{OUT} = 30 W CW
Dynamic Characteristics						
Input Capacitance	C_{GS}	–	8.2	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz
Output Capacitance	C_{DS}	–	1.7	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz
Feedback Capacitance	C_{GD}	–	0.4	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz

Notes:

[1] P_{SAT} is defined as I_G = 0.7 mA.

[2] Drain Efficiency = P_{OUT} / P_{DC}.

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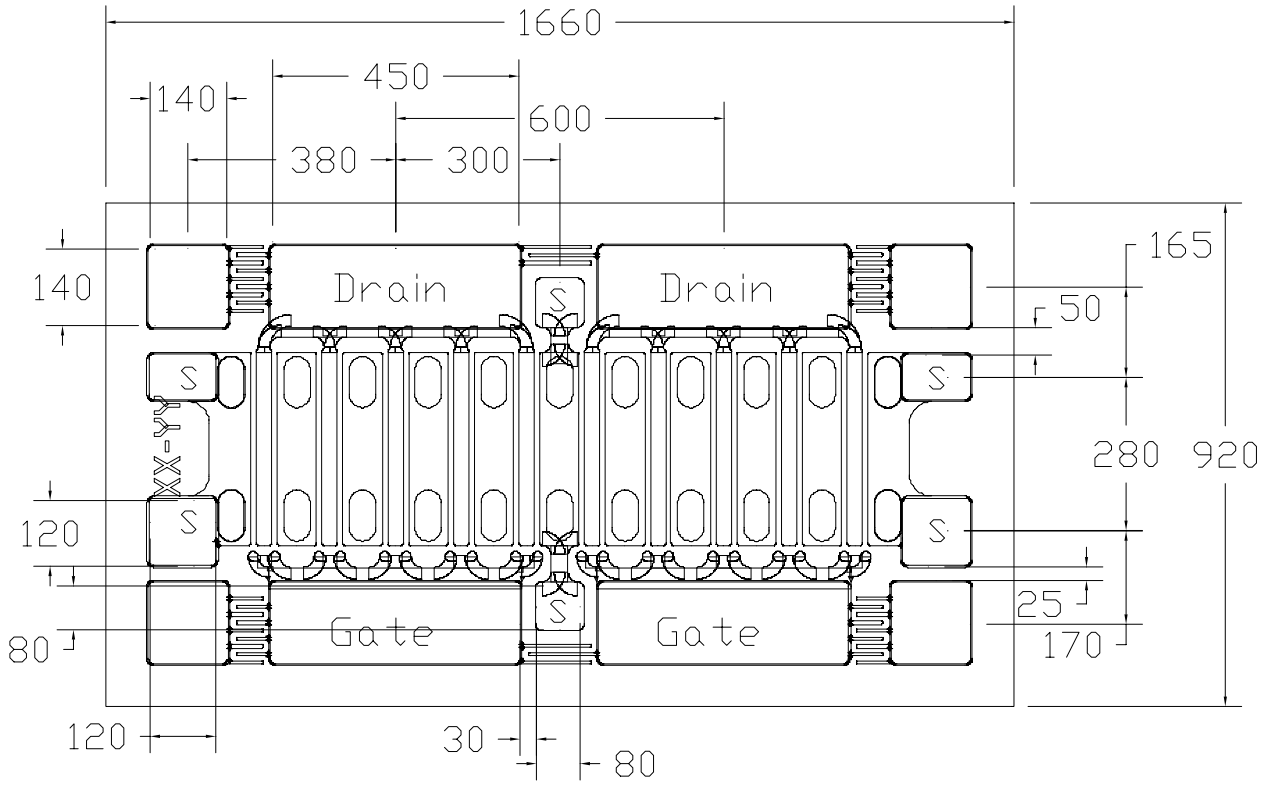
DIE Dimensions (units in microns)



Overall die size 1660 x 920 (+0/-50) microns, die thickness 100 (+/- 10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Assembly Notes:

- Recommended solder is AuSn (80/20) solder. Refer to Cree's website for the Eutectic Die Bond Procedure application note at http://www.cree.com/products/wireless_documents.asp
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.
- Use the die label (XX-YY) for correct orientation.

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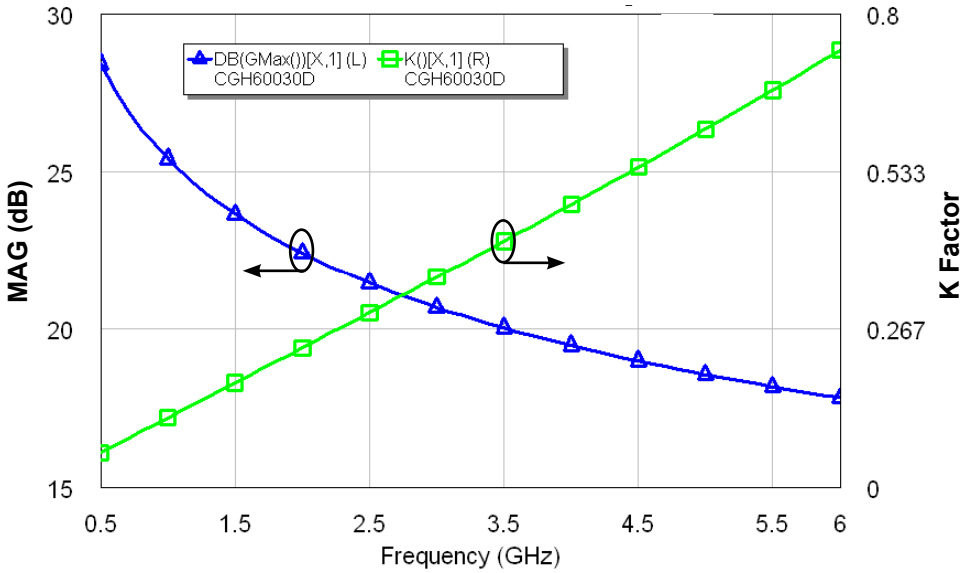
Typical Performance

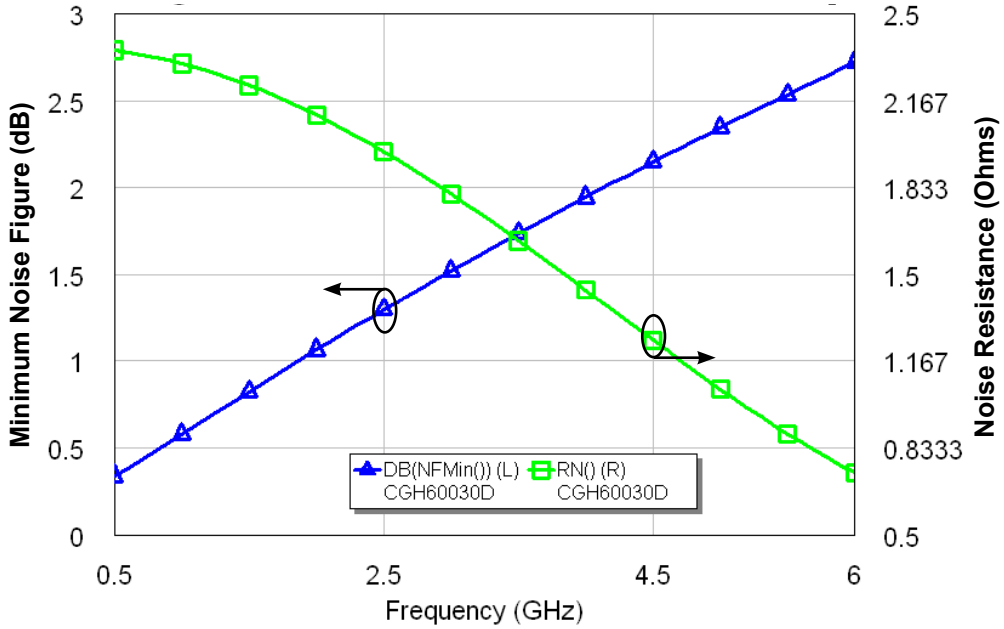
Simulated Maximum Available Gain and K Factor of the CGH60030D
V_{DD} = 28 V, I_{DQ} = 250 mA



Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Typical Noise Performance

Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH60030D
V_{DD} = 28 V, I_{DQ} = 250 mA



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Typical Die S-Parameters (Small Signal, V_{DS} = 28 V, I_{DQ} = 100 mA, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.928	-148.38	12.12	97.65	0.026	8.46	0.377	-137.96
600 MHz	0.927	-153.41	10.18	93.73	0.026	4.70	0.383	-141.15
700 MHz	0.926	-157.06	8.75	90.48	0.026	1.62	0.389	-143.08
800 MHz	0.926	-159.83	7.66	87.68	0.026	-1.02	0.397	-144.26
900 MHz	0.926	-162.00	6.80	85.17	0.026	-3.37	0.406	-144.97
1.0 GHz	0.927	-163.74	6.10	82.88	0.026	-5.49	0.415	-145.39
1.1 GHz	0.927	-165.17	5.53	80.75	0.026	-7.46	0.425	-145.63
1.2 GHz	0.927	-166.37	5.05	78.75	0.026	-9.30	0.435	-145.76
1.3 GHz	0.928	-167.39	4.64	76.85	0.026	-11.03	0.446	-145.83
1.4 GHz	0.929	-168.26	4.28	75.04	0.026	-12.68	0.457	-145.87
1.5 GHz	0.929	-169.03	3.97	73.30	0.026	-14.26	0.468	-145.91
1.6 GHz	0.930	-169.70	3.70	71.62	0.025	-15.78	0.479	-145.96
1.7 GHz	0.931	-170.30	3.46	69.99	0.025	-17.24	0.491	-146.02
1.8 GHz	0.932	-170.83	3.24	68.41	0.025	-18.66	0.502	-146.10
1.9 GHz	0.933	-171.31	3.04	66.88	0.025	-20.03	0.514	-146.22
2.0 GHz	0.934	-171.75	2.87	65.39	0.025	-21.36	0.525	-146.35
2.1 GHz	0.934	-172.16	2.71	63.93	0.024	-22.65	0.537	-146.52
2.2 GHz	0.935	-172.53	2.56	62.51	0.024	-23.90	0.548	-146.71
2.3 GHz	0.936	-172.87	2.43	61.13	0.024	-25.13	0.559	-146.92
2.4 GHz	0.937	-173.19	2.31	59.77	0.024	-26.32	0.570	-147.16
2.5 GHz	0.938	-173.49	2.19	58.45	0.024	-27.48	0.581	-147.42
2.6 GHz	0.939	-173.77	2.09	57.15	0.023	-28.61	0.592	-147.70
2.7 GHz	0.940	-174.04	1.99	55.89	0.023	-29.71	0.602	-147.99
2.8 GHz	0.941	-174.29	1.90	54.65	0.023	-30.79	0.613	-148.30
2.9 GHz	0.942	-174.53	1.82	53.44	0.023	-31.84	0.623	-148.63
3.0 GHz	0.943	-174.76	1.74	52.25	0.022	-32.86	0.633	-148.97
3.2 GHz	0.945	-175.19	1.60	49.95	0.022	-34.84	0.652	-149.67
3.4 GHz	0.947	-175.59	1.47	47.74	0.021	-36.72	0.670	-150.40
3.6 GHz	0.948	-175.97	1.36	45.62	0.021	-38.52	0.687	-151.16
3.8 GHz	0.950	-176.32	1.26	43.58	0.020	-40.23	0.703	-151.92
4.0 GHz	0.952	-176.65	1.17	41.62	0.020	-41.86	0.718	-152.69
4.2 GHz	0.953	-176.97	1.09	39.74	0.019	-43.42	0.732	-153.47
4.4 GHz	0.955	-177.28	1.02	37.92	0.019	-44.91	0.745	-154.24
4.6 GHz	0.956	-177.58	0.95	36.17	0.018	-46.33	0.758	-155.00
4.8 GHz	0.957	-177.86	0.89	34.49	0.018	-47.69	0.770	-155.75
5.0 GHz	0.959	-178.14	0.84	32.87	0.018	-48.99	0.781	-156.49
5.2 GHz	0.960	-178.41	0.79	31.30	0.017	-50.23	0.791	-157.22
5.4 GHz	0.961	-178.67	0.74	29.79	0.017	-51.41	0.801	-157.93
5.6 GHz	0.962	-178.92	0.70	28.33	0.016	-52.55	0.810	-158.62
5.8 GHz	0.963	-179.17	0.66	26.91	0.016	-53.64	0.819	-159.30
6.0 GHz	0.964	-179.42	0.62	25.54	0.015	-54.68	0.827	-159.97

To download the s-parameters in s2p format, go to the CGH60030D Product Page and click the documentation tab.

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Typical Die S-Parameters (Small Signal, V_{DS} = 28 V, I_{DQ} = 250 mA, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.942	-153.97	12.93	96.51	0.019	7.34	0.456	-157.13
600 MHz	0.941	-158.22	10.84	93.23	0.019	4.23	0.462	-158.92
700 MHz	0.941	-161.30	9.31	90.53	0.019	1.69	0.467	-159.94
800 MHz	0.941	-163.63	8.15	88.20	0.019	-0.48	0.472	-160.51
900 MHz	0.941	-165.46	7.24	86.11	0.019	-2.39	0.477	-160.77
1.0 GHz	0.941	-166.93	6.51	84.20	0.019	-4.13	0.483	-160.84
1.1 GHz	0.941	-168.14	5.90	82.43	0.019	-5.74	0.488	-160.78
1.2 GHz	0.941	-169.15	5.40	80.76	0.019	-7.24	0.494	-160.64
1.3 GHz	0.942	-170.02	4.96	79.17	0.018	-8.66	0.500	-160.45
1.4 GHz	0.942	-170.77	4.59	77.65	0.018	-10.02	0.506	-160.22
1.5 GHz	0.942	-171.42	4.27	76.18	0.018	-11.32	0.512	-159.98
1.6 GHz	0.943	-171.99	3.99	74.76	0.018	-12.57	0.519	-159.73
1.7 GHz	0.943	-172.50	3.73	73.38	0.018	-13.79	0.526	-159.49
1.8 GHz	0.944	-172.96	3.51	72.03	0.018	-14.97	0.533	-159.26
1.9 GHz	0.944	-173.38	3.31	70.72	0.018	-16.11	0.540	-159.04
2.0 GHz	0.945	-173.76	3.12	69.43	0.018	-17.23	0.547	-158.85
2.1 GHz	0.945	-174.10	2.96	68.18	0.018	-18.32	0.555	-158.67
2.2 GHz	0.946	-174.42	2.81	66.94	0.018	-19.39	0.562	-158.51
2.3 GHz	0.946	-174.72	2.67	65.73	0.018	-20.43	0.569	-158.38
2.4 GHz	0.947	-174.99	2.54	64.55	0.017	-21.45	0.577	-158.27
2.5 GHz	0.947	-175.25	2.42	63.38	0.017	-22.45	0.584	-158.18
2.6 GHz	0.948	-175.49	2.31	62.23	0.017	-23.43	0.592	-158.11
2.7 GHz	0.948	-175.72	2.21	61.10	0.017	-24.39	0.599	-158.07
2.8 GHz	0.949	-175.94	2.12	60.00	0.017	-25.33	0.607	-158.04
2.9 GHz	0.949	-176.14	2.03	58.90	0.017	-26.25	0.614	-158.03
3.0 GHz	0.950	-176.34	1.95	57.83	0.017	-27.16	0.621	-158.05
3.2 GHz	0.951	-176.71	1.80	55.73	0.016	-28.92	0.636	-158.12
3.4 GHz	0.952	-177.05	1.67	53.70	0.016	-30.62	0.650	-158.27
3.6 GHz	0.953	-177.37	1.55	51.73	0.016	-32.25	0.664	-158.46
3.8 GHz	0.954	-177.67	1.44	49.82	0.015	-33.83	0.677	-158.70
4.0 GHz	0.955	-177.95	1.35	47.97	0.015	-35.35	0.690	-158.99
4.2 GHz	0.957	-178.22	1.26	46.17	0.015	-36.81	0.702	-159.31
4.4 GHz	0.958	-178.48	1.18	44.42	0.015	-38.22	0.714	-159.66
4.6 GHz	0.959	-178.73	1.11	42.73	0.014	-39.57	0.726	-160.03
4.8 GHz	0.960	-178.98	1.05	41.09	0.014	-40.88	0.737	-160.42
5.0 GHz	0.961	-179.21	0.99	39.49	0.014	-42.14	0.747	-160.82
5.2 GHz	0.961	-179.44	0.93	37.94	0.013	-43.36	0.757	-161.24
5.4 GHz	0.962	-179.67	0.88	36.43	0.013	-44.53	0.767	-161.67
5.6 GHz	0.963	-179.89	0.84	34.96	0.013	-45.65	0.776	-162.11
5.8 GHz	0.964	179.90	0.79	33.54	0.013	-46.74	0.784	-162.55
6.0 GHz	0.965	179.68	0.75	32.15	0.012	-47.79	0.793	-162.99

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Typical Die S-Parameters (Small Signal, V_{DS} = 28 V, I_{DQ} = 400 mA, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.948	-155.97	12.94	96.03	0.016	6.87	0.489	-162.06
600 MHz	0.948	-159.93	10.84	92.98	0.016	3.99	0.495	-163.44
700 MHz	0.947	-162.79	9.31	90.46	0.016	1.65	0.499	-164.22
800 MHz	0.947	-164.96	8.15	88.28	0.016	-0.36	0.503	-164.63
900 MHz	0.947	-166.67	7.24	86.34	0.016	-2.13	0.507	-164.80
1.0 GHz	0.947	-168.04	6.51	84.56	0.016	-3.73	0.512	-164.82
1.1 GHz	0.947	-169.17	5.90	82.91	0.016	-5.21	0.516	-164.72
1.2 GHz	0.948	-170.12	5.40	81.35	0.016	-6.60	0.521	-164.56
1.3 GHz	0.948	-170.93	4.97	79.86	0.016	-7.91	0.525	-164.35
1.4 GHz	0.948	-171.63	4.60	78.44	0.016	-9.17	0.530	-164.11
1.5 GHz	0.948	-172.24	4.28	77.06	0.016	-10.37	0.535	-163.85
1.6 GHz	0.949	-172.78	4.00	75.73	0.016	-11.53	0.541	-163.59
1.7 GHz	0.949	-173.27	3.75	74.43	0.016	-12.66	0.546	-163.33
1.8 GHz	0.949	-173.70	3.52	73.17	0.016	-13.75	0.552	-163.07
1.9 GHz	0.949	-174.09	3.32	71.93	0.016	-14.82	0.558	-162.82
2.0 GHz	0.950	-174.45	3.14	70.72	0.015	-15.86	0.563	-162.59
2.1 GHz	0.950	-174.78	2.98	69.53	0.015	-16.87	0.569	-162.37
2.2 GHz	0.951	-175.08	2.83	68.37	0.015	-17.87	0.576	-162.17
2.3 GHz	0.951	-175.36	2.69	67.22	0.015	-18.84	0.582	-161.99
2.4 GHz	0.951	-175.62	2.56	66.09	0.015	-19.79	0.588	-161.82
2.5 GHz	0.952	-175.87	2.45	64.98	0.015	-20.73	0.594	-161.67
2.6 GHz	0.952	-176.10	2.34	63.89	0.015	-21.65	0.601	-161.54
2.7 GHz	0.953	-176.31	2.24	62.82	0.015	-22.55	0.607	-161.43
2.8 GHz	0.953	-176.52	2.15	61.76	0.015	-23.44	0.613	-161.34
2.9 GHz	0.953	-176.72	2.06	60.72	0.015	-24.31	0.619	-161.27
3.0 GHz	0.954	-176.90	1.98	59.69	0.015	-25.16	0.626	-161.21
3.2 GHz	0.955	-177.25	1.83	57.68	0.014	-26.83	0.638	-161.15
3.4 GHz	0.956	-177.58	1.70	55.72	0.014	-28.44	0.651	-161.14
3.6 GHz	0.957	-177.88	1.58	53.82	0.014	-30.00	0.663	-161.19
3.8 GHz	0.957	-178.16	1.47	51.97	0.014	-31.51	0.675	-161.30
4.0 GHz	0.958	-178.43	1.38	50.16	0.013	-32.96	0.686	-161.44
4.2 GHz	0.959	-178.69	1.29	48.41	0.013	-34.37	0.698	-161.63
4.4 GHz	0.960	-178.94	1.22	46.71	0.013	-35.73	0.709	-161.84
4.6 GHz	0.961	-179.18	1.14	45.05	0.013	-37.04	0.719	-162.09
4.8 GHz	0.962	-179.41	1.08	43.43	0.012	-38.31	0.729	-162.36
5.0 GHz	0.962	-179.63	1.02	41.85	0.012	-39.54	0.739	-162.66
5.2 GHz	0.963	-179.85	0.96	40.32	0.012	-40.72	0.749	-162.97
5.4 GHz	0.964	179.93	0.91	38.83	0.012	-41.87	0.758	-163.30
5.6 GHz	0.965	179.72	0.87	37.37	0.012	-42.97	0.767	-163.64
5.8 GHz	0.965	179.52	0.82	35.95	0.011	-44.04	0.775	-163.99
6.0 GHz	0.966	179.32	0.78	34.57	0.011	-45.07	0.783	-164.35

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Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A (> 250 V)	JEDEC JESD22 A114-D
Charge Device Model	CDM	II (200 < 500 V)	JEDEC JESD22 C101-C

Product Ordering Information

Order Number	Description	Unit of Measure
CGH60030D	GaN HEMT Bare Die	Each

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Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
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Данный компонент на территории Российской Федерации

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http://moschip.ru/get-element

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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